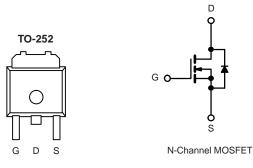


N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)			
60	0.074 at V _{GS} = 10 V	20	6.5 nC			
60	0.078 at V _{GS} = 4.5 V	13	0.5 110			



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET ٠
- •
- 100 % R_g and UIS Tested Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

DC/DC Converters



RoHS COMPLIANT HALOGEN FREE

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	60	V		
Gate-Source Voltage		V _{GS}	± 20	V	
	T _C = 25 °C		20	_	
Continuous Drain Current $(T_{-} = 150 ^{\circ}\text{C})$	T _C = 70 °C		12.1		
Continuous Drain Current ($T_J = 150 \text{ °C}$)	T _A = 25 °C	I _D	9.1 ^a		
	T _A = 70 °C		7.6 ^a	Α	
Pulsed Drain Current	I _{DM}	60			
Continuous Source-Drain Diode Current	T _C = 25 °C		17.8		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	3.8 ^a		
Single Pulse Avalanche Current L = 0.1 mH Avalanche Energy L = 0.1 mH		I _{AS}	20		
		E _{AS}	26	mJ	
	T _C = 25 °C		31.25		
Maximum Dawar Disaination	T _C = 70 °C	D D	20	w	
Maximum Power Dissipation	T _A = 25 °C	P _D	5.7 ^a	V	
	T _A = 70 °C		3.6 ^a	7	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambienta	$t \le 10 \text{ s}$	R _{thJA}	18	22	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	3.2	4.0	0/10	

Notes:

a. Surface mounted on 1" x 1" FR4 board, t \leq 10 s.

SPECIFICATIONS ($T_J = 25 \circ 0$	I			1	1	1	
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	60			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	- Ι _D = 250 μΑ		65		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	iD = 200 μA		- 6.3			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			1	μA	
Zero Gale vollage Drain Current	I _{DSS}				20		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	50			А	
Drain Source On State Registered	Р	V _{GS} = 10 V, I _D = 8 A		0.074	0.081	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 6 A		0.078	0.089		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 11 A		20		S	
Dynamic ^b		·			·		
Input Capacitance	C _{iss}			670		pF	
Output Capacitance	C _{oss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		140			
Reverse Transfer Capacitance	C _{rss}			60			
Takal Qada Qhaasa	Q_{g} $V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 13 \text{ A}$		11	17			
Total Gate Charge				6.5	13	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 13 \text{ A}$		3.0			
Gate-Drain Charge	Q _{gd}			3.0			
Gate Resistance	R _g	f = 1 MHz		1.6	3.2	Ω	
Turn-On Delay Time	t _{d(on)}			18	30	-	
Rise Time	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_{1} = 1.3 \Omega$		250	400		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 13$ Å, $V_{GEN} = 4.5$ V, $R_g = 1 \Omega$		35	55		
Fall Time	t _f			68	110	1	
Turn-On Delay Time	t _{d(on)}			8	15	ns	
Rise Time	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_{1} = 1.3 \Omega$		15	25	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 13$ Å, $V_{GEN} = 10$ V, $R_g = 1 \Omega$		30	45		
Fall Time	t _f			25	40		
Drain-Source Body Diode Characteris		· · · · · · · · · · · · · · · · · · ·					
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			20	_	
Pulse Diode Forward Current ^a	I _{SM}				60	A	
Body Diode Voltage	V _{SD}	I _S = 11 A		1.0	1.5	V	
Body Diode Reverse Recovery Time	t _{rr}			30	60	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	<u>-</u>		35	70	nC	
Reverse Recovery Fall Time	t _a	· I _F = 11 A, dl/dt = 100 A/μs, T _J = 25 °C		20			
Reverse Recovery Rise Time	t _b	1		10		ns	

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



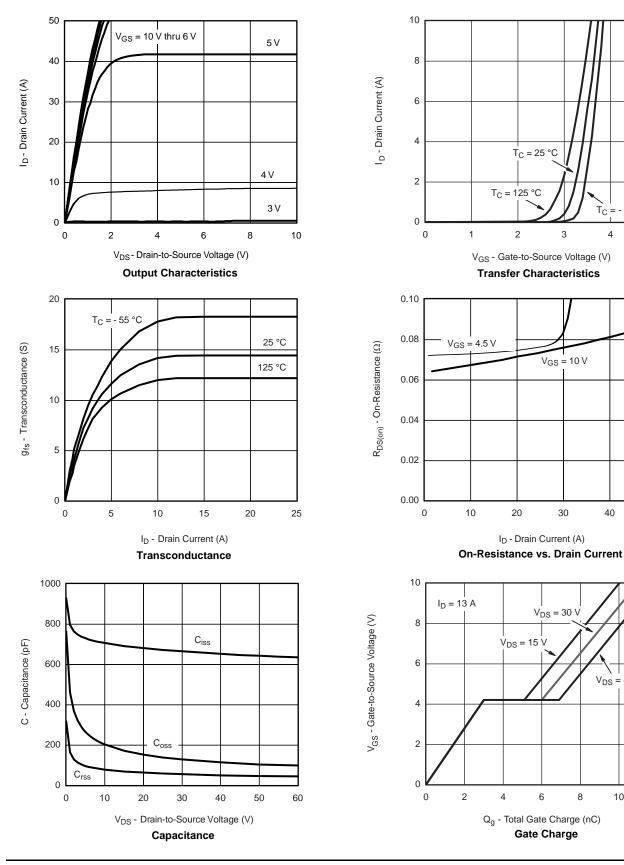
T_C = - 55 °C

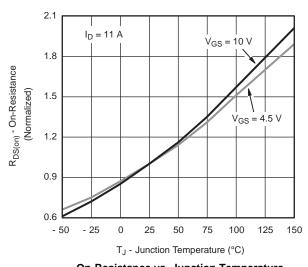
V_{GS} = 10 V

 $V_{DS} = 30 V$

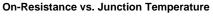
 $V_{DS} = 45 V$

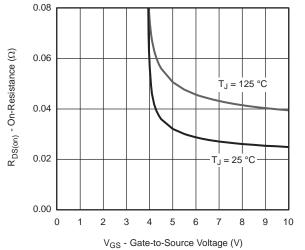
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



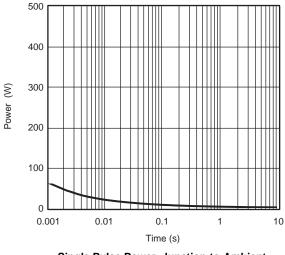


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

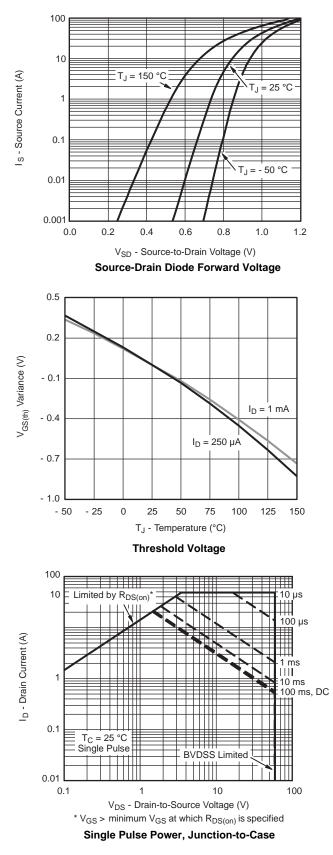






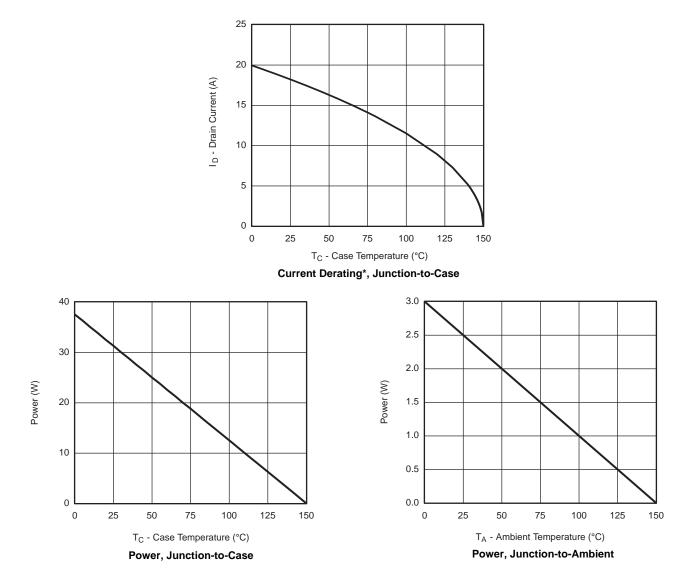


Single Pulse Power, Junction-to-Ambient



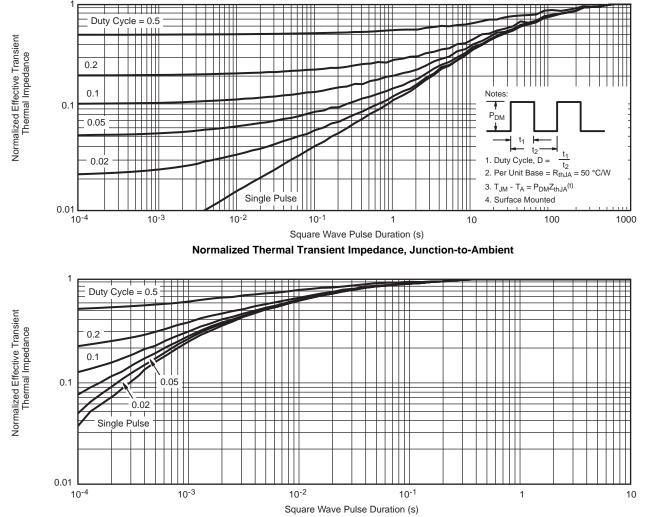


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



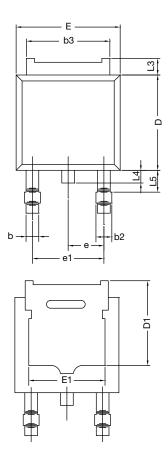
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case







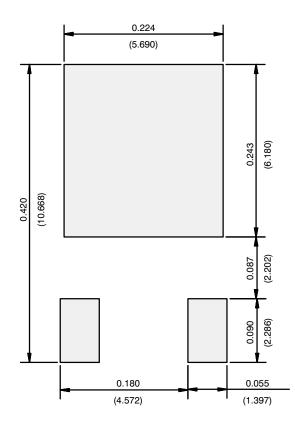
	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	3SC 0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

www.din-tek.jp

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Din-Tek Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Din-Tek"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Din-Tek makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Din-Tek disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Din-Tek's knowledge of typical requirements that are often placed on Din-Tek products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Din-Tek's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Din-Tek products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Din-Tek product could result in personal injury or death. Customers using or selling Din-Tek products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Din-Tek personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Din-Tek. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Din-Tek documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Din-Tek documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.